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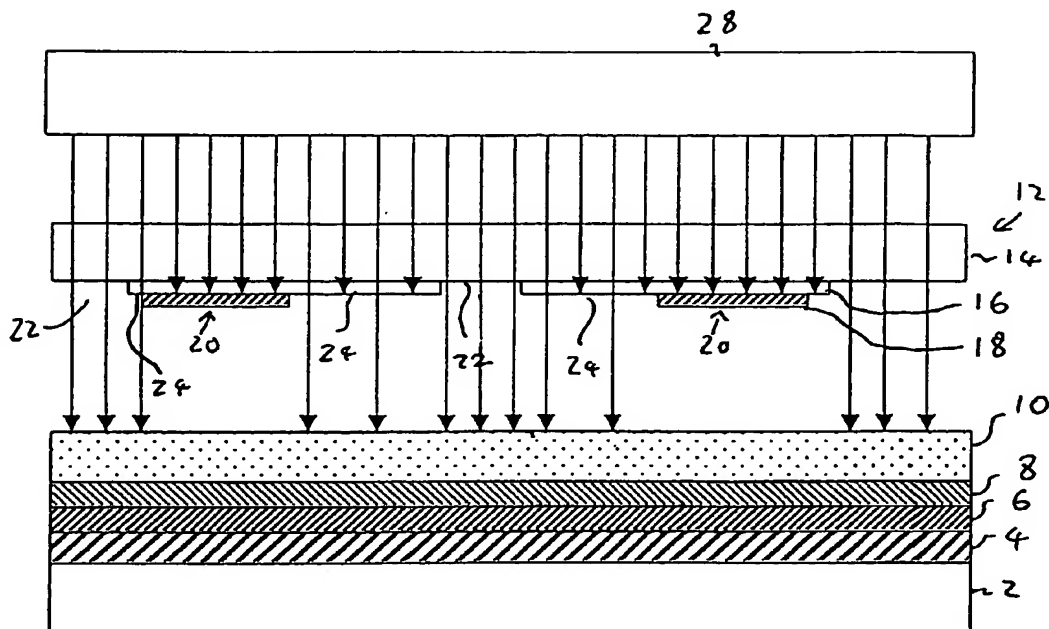
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[Continued on next page]

(54) Title: MASK AND MANUFACTURING METHOD USING MASK



(57) Abstract: A mask 12 includes half-tone layer 16 and light blocking layer 20. The half-tone layer 16 is of silicon rich silicon nitride SiN_xH . x may be in the range 0 to 1, preferably 0.2 to 0.6, so that the optical band gap can be in the range 2.1eV to 2.5eV. It has been discovered that photoresist removal when the mask 12 is used is very dependent on the band gap, and not too dependent on the thickness, so good control of TFT manufacture can be obtained.

WO 2004/006016 A3